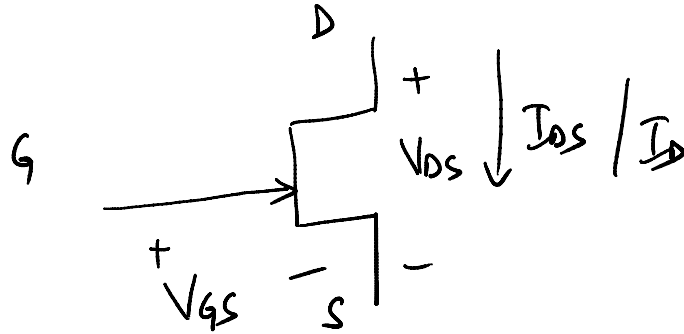


# LECTURE-33

n-CHANNEL JFET  $\rightarrow$  nFET



$V_{DS} \rightarrow$  DRAIN TO SOURCE VOLTAGE  
 $I_{DS} \rightarrow$  " " " CURRENT  
 $V_{GS} \rightarrow$  GATE TO SOURCE VOLTAGE

$V_p$   $\rightarrow$  PINCH-OFF VOLTAGE  $\rightarrow$  GATE-CHANNEL  
RB VOLTAGE FOR WHICH OPPOSITE DEPLETION  
REGIONS MERGE

( $V_{p0}$ )

$I_{DSS}$   $\rightarrow$  DRAIN TO SOURCE SATURATION CURRENT  
(MAXIMUM CURRENT THAT FLOWS IN nFET  
WHEN THE DEVICE IS NORMALLY ON)  
SPECIFIED AT  $V_{GS} = 0V$

## 3 REGIONS OF OPERATION

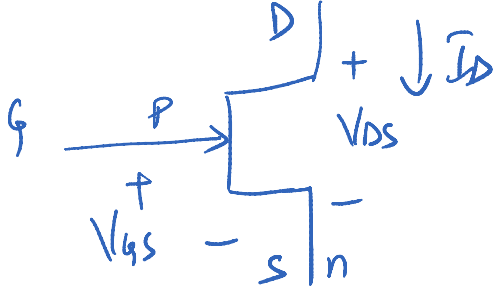
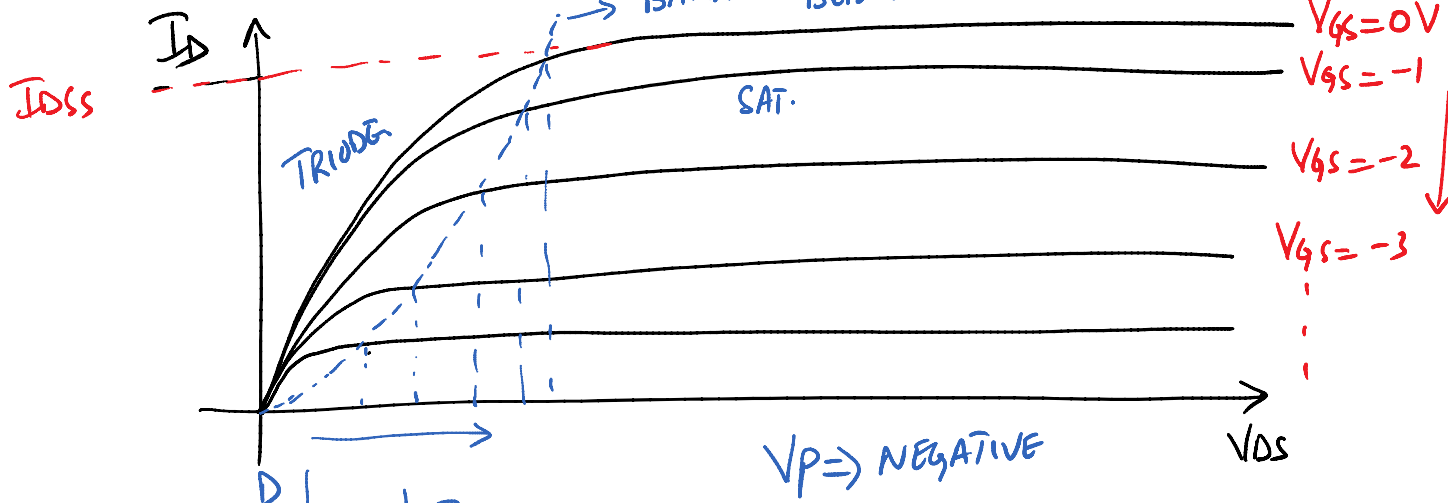
- ① CUTOFF
- ② SATURATION
- ③ TRIODE / NON SATURATION

## TRANSISTOR IN SATURATION

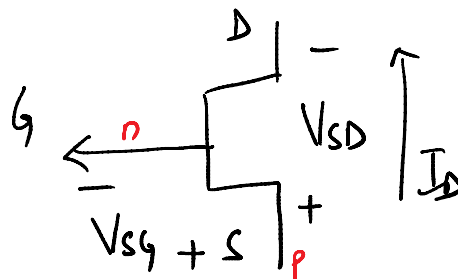
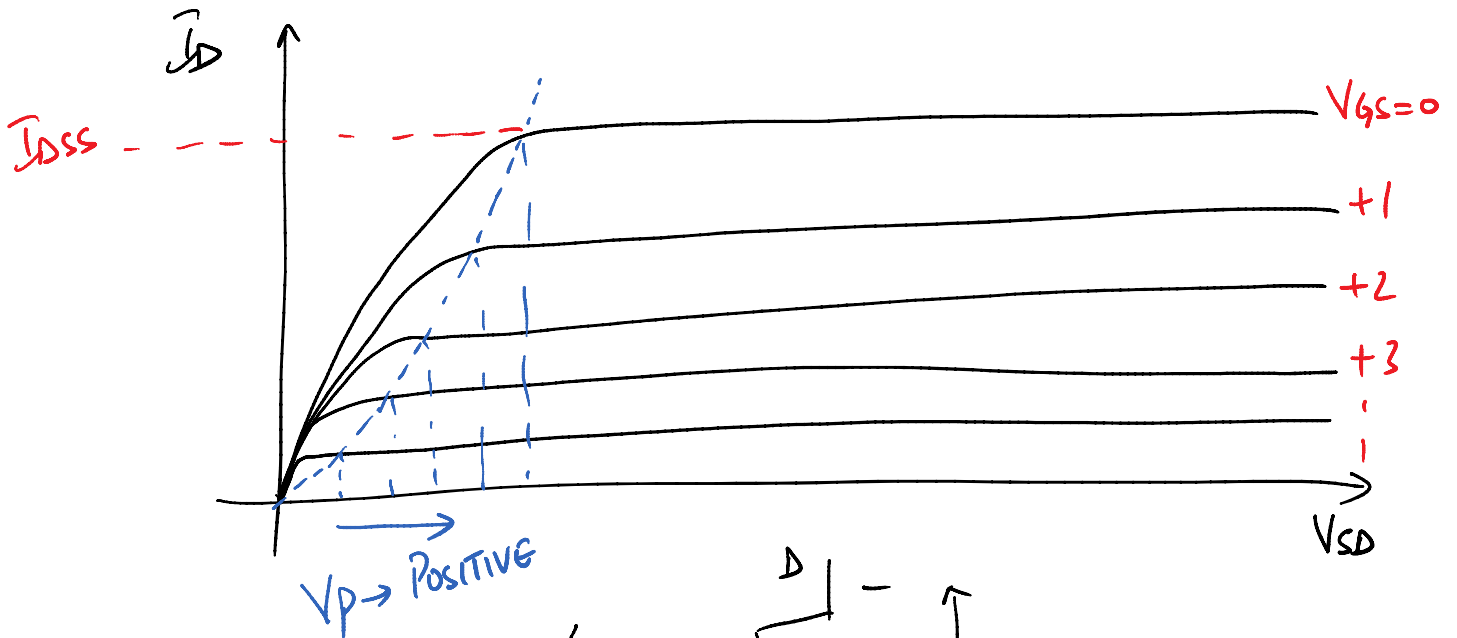
$$I_{DS} = I_D = I_{DSS} \left[ 1 - \frac{V_{GS}}{V_p} \right]^2$$

→  $V_p$  NEGATIVE FOR nFET  
POSITIVE FOR pFET

# nFET CHARACTERISTICS



PnFET



$V_{GS}$  NEGATIVE  
OR  
 $V_{GS}$  POSITIVE

IN SAT.

$$I_D = I_{DSS} \left[ 1 - \frac{V_{GS}}{V_P} \right]^2$$

NJFET

$V_P$  IS NEGATIVE,  $V_{GS}$  NEGATIVE

$\therefore \frac{V_{GS}}{V_P}$  IS POSITIVE

PJFET

$V_P$  IS POSITIVE

$V_{GS}$  IS POSITIVE

$\therefore \frac{V_{GS}}{V_P} \Rightarrow$  POSITIVE

nJFET

SATURATION OCCURS WHEN  $V_{DS} \geq \underline{\underline{V_{DS(SAT)}}}$

POSITIVE ←  $V_{DS(SAT)} = V_{GS} - V_P$

PJFET

SATURATION OCCURS WHEN  $V_{SD} \geq V_{SD(SAT)}$

POSITIVE ←  $V_{SD(SAT)} = V_P - V_{GS}$

n JFET  
IN SATURATION

$$I_D = I_{DSS} \left(1 - \frac{V_{GS}}{V_P}\right)^2$$

$$V_{DS} \geq V_{DS(SAT)}$$

$$V_{DS(SAT)} = V_{GS} - V_P$$

$$\therefore V_{DS} \geq V_{GS} - V_P$$

TRIODE REGION

$V_{DS} = V_{GS} - V_P$  IS TRANSITION POINT

$V_{GS} = V_{DS} + V_P$  → THRESHOLD POINT

IN TRIODE REGION

$$I_D = I_{DSS} \left[ 2 \left( 1 - \frac{V_{GS}}{V_P} \right) \left( \frac{V_{DS}}{-V_P} \right) - \left( \frac{V_{DS}}{V_P} \right)^2 \right]$$

AT TRANSITION POINT

$$V_{DS} = V_{GS} - V_P$$

$$I_D = I_{DSS} \left[ 2 \left( 1 - \frac{V_{GS}}{V_P} \right) \left( \frac{V_{GS} - V_P}{-V_P} \right) - \left( \frac{V_{GS} - V_P}{V_P} \right)^2 \right]$$

$$= I_{DSS} \left[ 2 \left( 1 - \frac{V_{GS}}{V_P} \right) \left( \frac{V_P - V_{GS}}{V_P} \right) - \left( \frac{V_{GS}}{V_P} - 1 \right)^2 \right]$$

$$= I_{DSS} \left[ 2 \left( 1 - \frac{V_{GS}}{V_P} \right) \left( 1 - \frac{V_{GS}}{V_P} \right) - \left( 1 - \frac{V_{GS}}{V_P} \right)^2 \right]$$

$$= I_{DSS} \left[ 2 \left( 1 - \frac{V_{GS}}{V_P} \right)^2 - \left( 1 - \frac{V_{GS}}{V_P} \right)^2 \right]$$

$$I_D = I_{DSS} \left[ 1 - \frac{V_{GS}}{V_P} \right]^2 \rightarrow \text{SAT. REGION}$$

$$I_D = I_{DSS} \left[ 1 - \frac{V_{GS}}{V_P} \right]^2 \rightarrow \text{SAT. REGION}$$



## P-CHANNEL PJFET

$$I_D = I_{DSS} \left( 1 - \frac{V_{GS}}{V_P} \right)^2$$

$$V_{SD} \geq V_{SD(SAT)}$$

$$V_{SD(SAT)} = V_P - V_{GS}$$

$$V_{SD} \geq V_P - V_{GS} \rightarrow \text{FOR SAT.}$$

IF  $V_{SD} < V_P - V_{GS} \rightarrow$  THEN IN THE TRIODE REGION

$$\boxed{V_{SD} = V_P - V_{GS}} \rightarrow \text{TRANSITION POINT}$$

$$I_D = I_{DSS} \left[ 2 \left( 1 - \frac{V_{GS}}{V_P} \right) \left( \frac{V_{SD}}{V_P} \right) - \left( \frac{V_{SD}}{V_P} \right)^2 \right]$$

DERIVATION LEFT TO STUDENTS!

# VOLTAGE TRANSFER CHARACTERISTICS

